

SMAF Plastic-Encapsulate Diodes

US1AF THRU US1MF High Efficient Rectifier Diodes

Features

- $I_{F(AV)}$ 1A
- V_{RRM} 50V-1000V
- High surge current capability
- Polarity: Color band denotes cathode

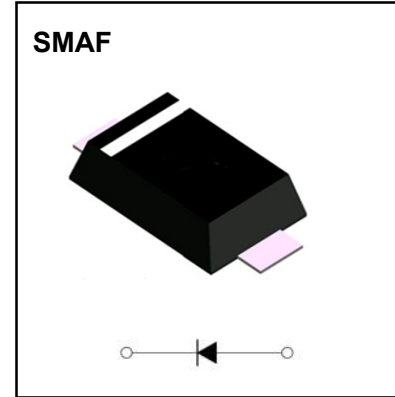
Applications

- Rectifier

Marking

- US1X

X : From A To M



Limiting Values(Absolute Maximum Rating)

Item	Symbol	Unit	Test Conditions	US1						
				AF	BF	DF	GF	JF	KF	MF
Repetitive Peak Reverse Voltage	V_{RRM}	V		50	100	200	400	600	800	1000
Maximum RMS Voltage	V_{RMS}	V		35	70	140	280	420	560	700
Average Forward Current	$I_{F(AV)}$	A	60Hz Half-sine wave, Resistance load	1.0						
Surge(Non-repetitive)Forward Current	I_{FSM}	A	60Hz Half-sine wave, 1 cycle, $T_a=25^{\circ}\text{C}$	30						
Operation Junction and Storage Temperature Range	T_J, T_{STG}	$^{\circ}\text{C}$		-55 ~ +150						

Electrical Characteristics ($T=25^{\circ}\text{C}$ Unless otherwise specified)

Item	Symbol	Unit	Test Condition		US1						
					AF	BF	DF	GF	JF	KF	MF
Peak Forward Voltage	V _F	V	I _F =1.0A		1.0			1.3	1.7		
Maximum reverse recovery time	t _{rr}	ns	I _F =0.5A,I _R =1.0A,I _{rr} =0.25A		50				75		
Peak Reverse Current	I _{RRM1}	μA	V _{RM} =V _{RRM}	T _a =25℃	5						
	T _a =125℃			50							
Thermal Resistance(Typical)	R _{θJ-A}	℃/W	Between junction and ambient		92						
	R _{θJ-L}		Between junction and terminal		10						
Juction Capacitance (Typical)	Cj	pF	Measured at 1MHZ and Applied Reverse Voltage of 4.0 V.D.C		14			12	6		

Notes:

Thermal resistance from junction to ambient and from junction to lead mounted on FR4 PCB double sided copper mini pad

Typical Characteristics

FIG.1: FORWARD CURRENT DERATING CURVE

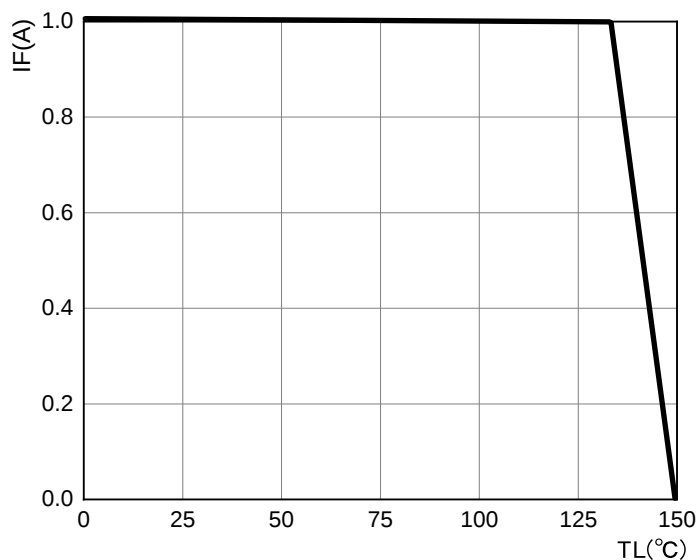
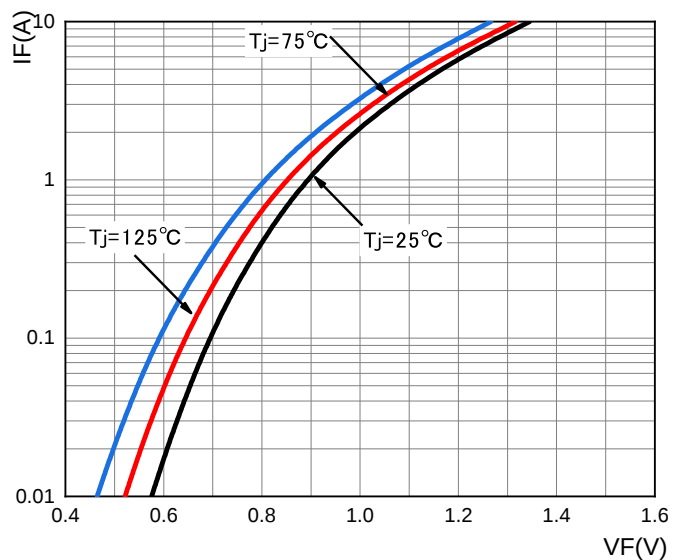


FIG 2: MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT



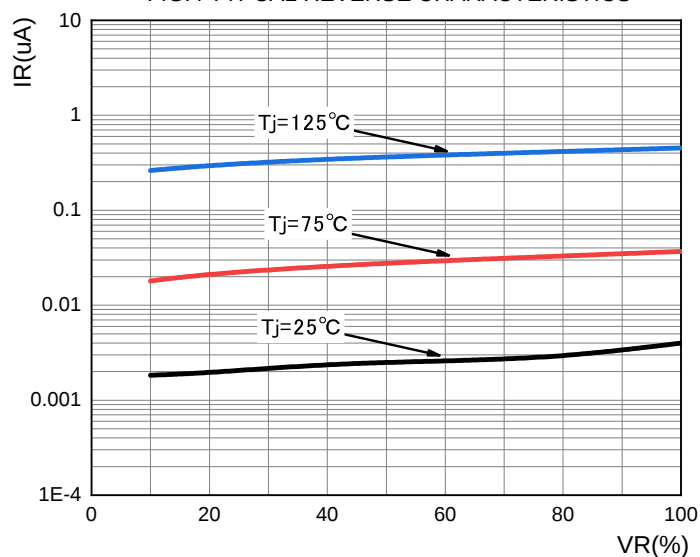
US1AF-US1DF

FIG.3 : TYPICAL FORWARD CHARACTERISTICS



US1AF-US1DF

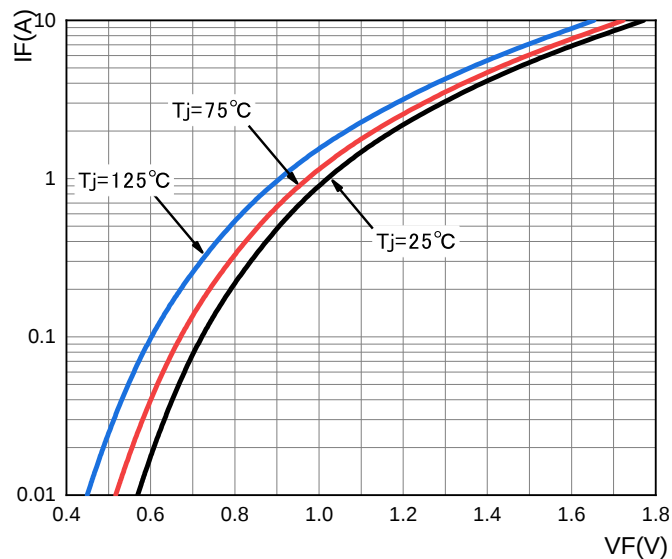
FIG.4 TYPICAL REVERSE CHARACTERISTICS



Typical Characteristics

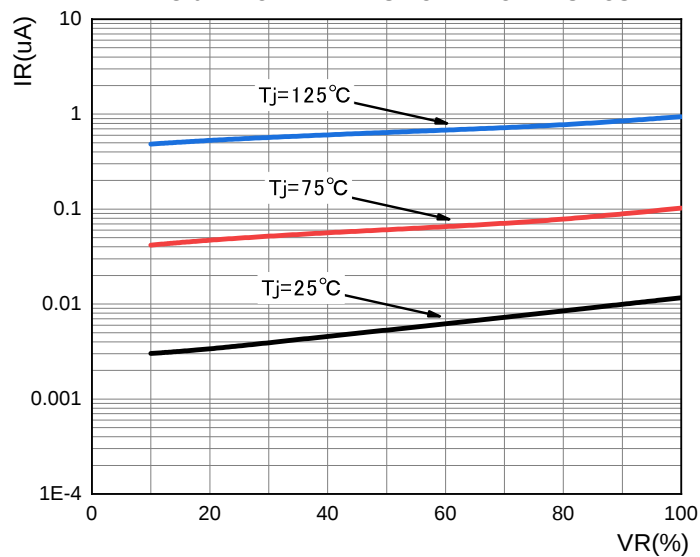
US1GF

FIG.5 : TYPICAL FORWARD CHARACTERISTICS



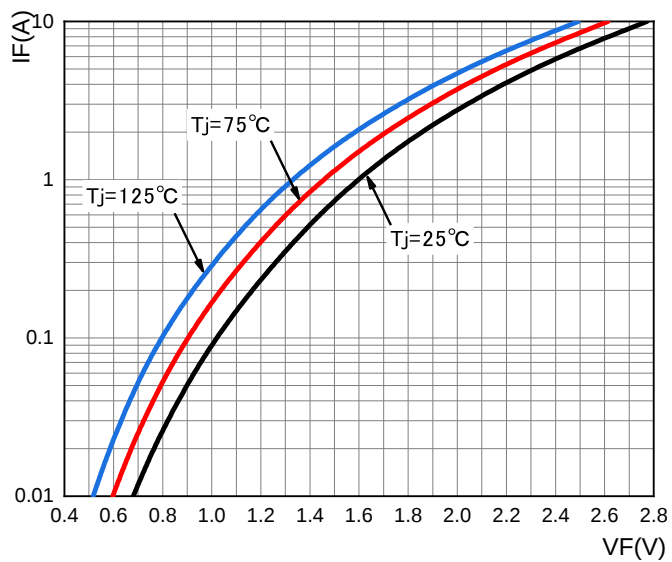
US1GF

FIG.6 TYPICAL REVERSE CHARACTERISTICS



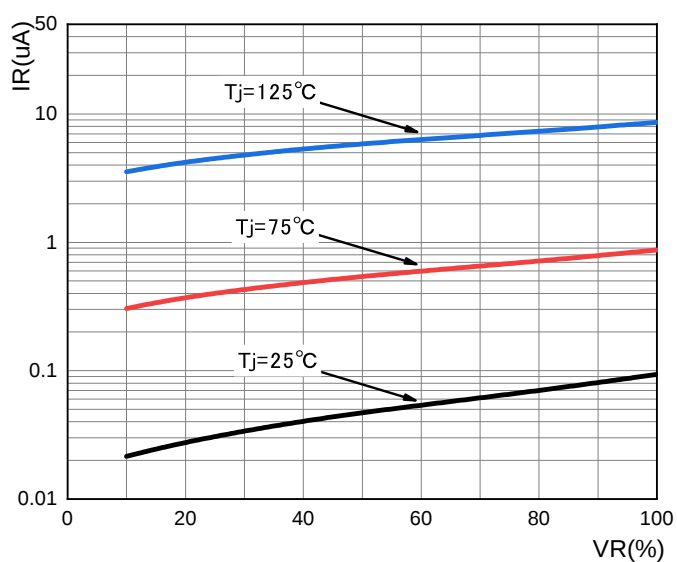
US1JF-US1MF

FIG.7 : TYPICAL FORWARD CHARACTERISTICS

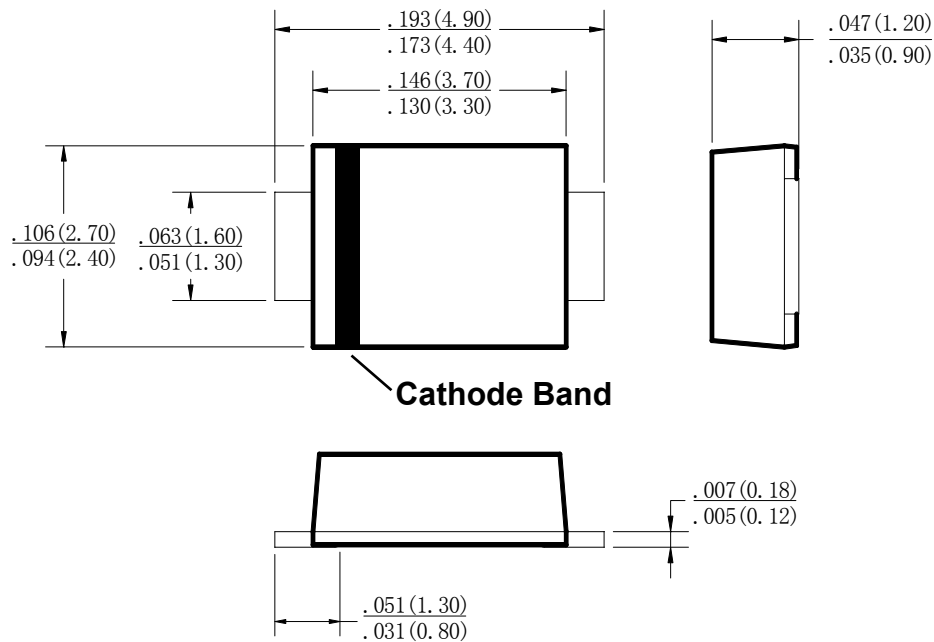


US1JF-US1MF

FIG.8 TYPICAL REVERSE CHARACTERISTICS

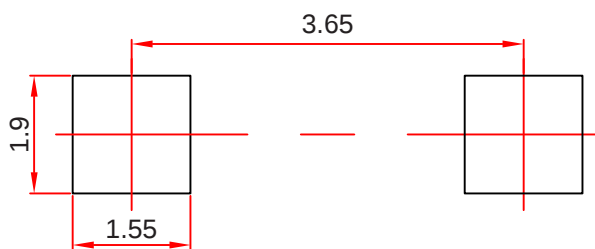


SMAF Package Outline Dimensions



Dimensions in inches and (millimeters)

SMAF Suggested Pad Layout



Note:

1. Controlling dimension: in millimeters.
2. General tolerance: ± 0.05 mm.
3. The pad layout is for reference purposes only.

NOTICE

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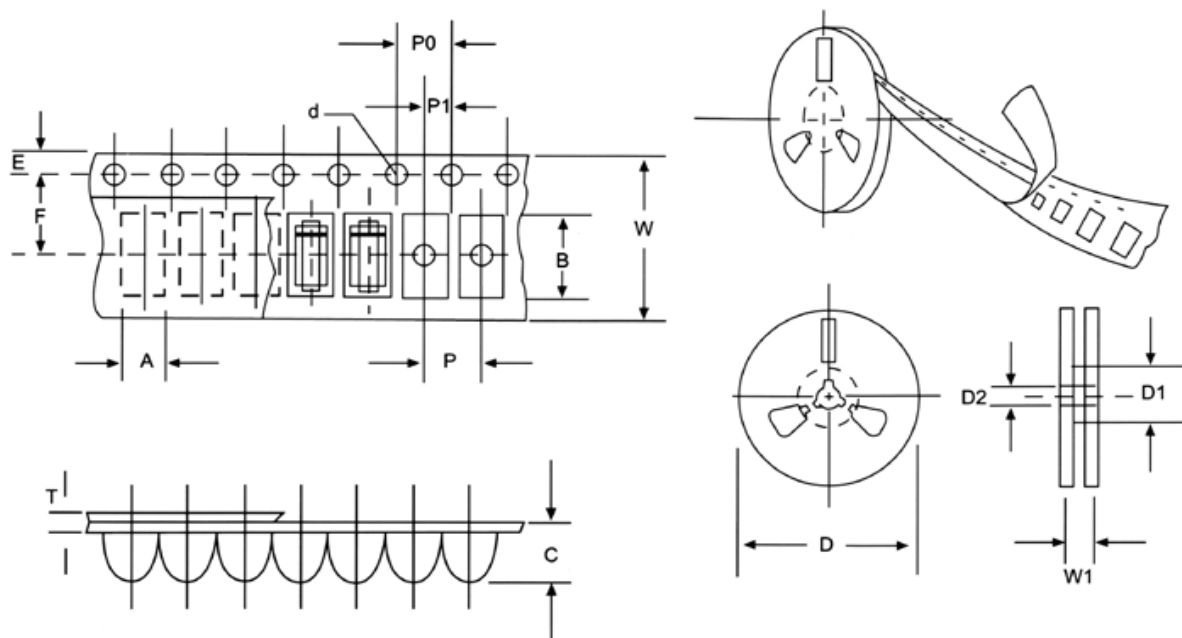


FIG:CONFIGURATION OF SURFACE MOUNTED DEVICES TAPING

ITEM	SYMBOL	SMAF mm(inch)
Carrier width	A	2.83±0.1(0.112±0.004)
Carrier length	B	4.90±0.1(0.193±0.004)
Carrier depth	C	1.45±0.1(0.057±0.004)
Sprocket hole	d	1.55±0.05(0.061±0.002)
Reel outside diameter	D	178±2.0(7.0±0.079)
Reel inner diameter	D1	54±1.0(2.13±0.039)
Feed hole diameter	D2	13±0.5(0.512±0.020)
Strocket hole position	E	1.75±0.1(0.069±0.004)
Punch hole position	F	5.5±0.05(0.217±0.002)
Punch hole pitch	P	4.0±0.1(0.157±0.004)
Sprocket hole pitch	P0	4.0±0.1(0.157±0.004)
Embossment center	P1	2.0±0.1(0.079±0.004)
Totall tape thickness	T	0.23-0.29(0.009-0.011)
Tape width	W	12.0±0.1(0.472±0.004)
Reel width	W1	16.8±2.0(0.661±0.079)

NOTE:Devices are packde in accordance with EIA standard RS-481-A and specification given above.